

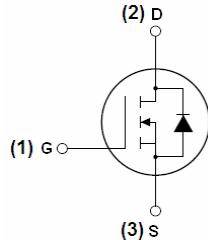
## General Features

VDSS	RDS(ON) @10V (typ)	ID
650V	330mΩ	11A

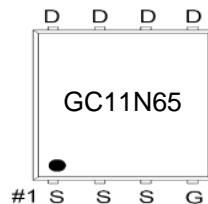
- Optimized for high speed smooth switching
- Enhanced Body diode dv/dt capability
- Enhanced Avalanche Ruggedness
- 100% UIS Tested, 100% Rg Tested
- RoHS Compliant

## Application

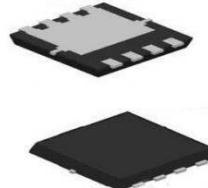
- DC-DC Conversion
- Hard Switching and High Speed Circuit
- Power Tools
- UPS
- SSR



Schematic diagram



Marking and pin assignment



DFN 5x6-8L

## Ordering Information

Part Number	Marking	Case	Packaging
GC11N65D5	GC11N65	DFN5*6-8L	5000pcs/Reel

## Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25^\circ\text{C}$	11	A
		$T_C=100^\circ\text{C}$	6	
Drain to Source Voltage	$V_{DS}$	-	650	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 30$	V
Pulsed Drain Current	$I_{DM}$	-	33	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=10 \text{ mH}, T_C=25^\circ\text{C}$	211	mJ
Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	78	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 150	°C

## Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	$R_{eJC}$	1.6	°C/W
Thermal Resistance Junction-Ambient	$R_{eJA}$	62	°C/W

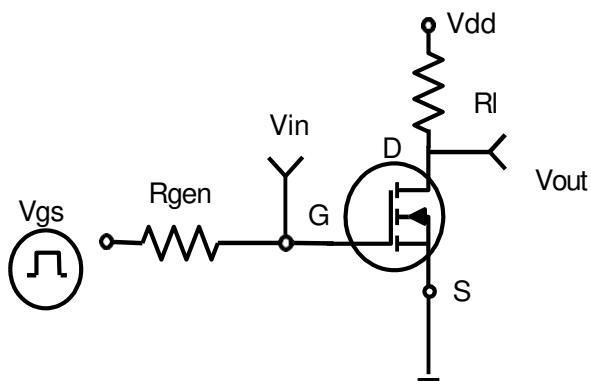
Electrical Characteristics at  $T_j=25^\circ\text{C}$  (unless otherwise specified)

Static Characteristics						
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$	650	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}, I_D=250\mu\text{A}$	2.5	-	4	
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=650\text{V}, T_j=25^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=650\text{V}, T_j=100^\circ\text{C}$	-	-	100	
Gate to Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 30\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
Drain to Source on Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_D=5.5\text{A}$	-	330	360	$\text{m}\Omega$
Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=10\text{V}, I_D=5.5\text{A}$	-	-	-	S

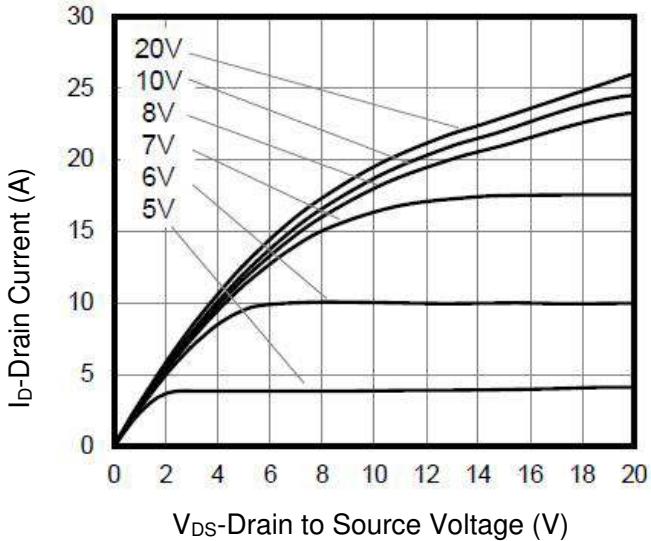
Dynamic Characteristics						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=50\text{V}, f=1\text{MHz}$	-	901	-	pF
Output Capacitance	$C_{\text{oss}}$		-	50	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	5.5	-	
Total Gate Charge	$Q_g$	$V_{\text{DD}}=520\text{V}, I_D=11\text{A}, V_{\text{GS}}=0\text{V}$	-	21	-	nC
Gate to Source Charge	$Q_{\text{gs}}$		-	4.5	-	
Gate to Drain (Miller) Charge	$Q_{\text{gd}}$		-	7	-	
Turn on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=400\text{V}, I_b=11\text{A}, V_{\text{GS}}=10\text{V}, R_G=25\Omega,$	-	42	-	ns
Rise time	$t_r$		-	20	-	
Turn off Delay Time	$t_{\text{d}(\text{off})}$		-	123	-	
Fall Time	$t_f$		-	6.4	-	

Reverse Diode Characteristics						
Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_F=11\text{A}$	-	-	1.4	V
Reverse Recovery Time	$t_{\text{rr}}$	$VR=400\text{V}, IF=11\text{A}, \frac{dI}{dt}=100\text{A}/\mu\text{s}$	-	280	-	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		-	2.8	-	nC

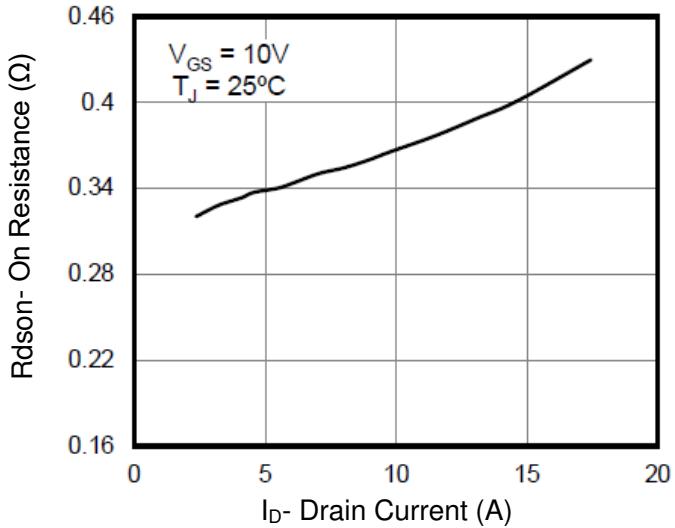
## Typical Electrical And Thermal Characteristics



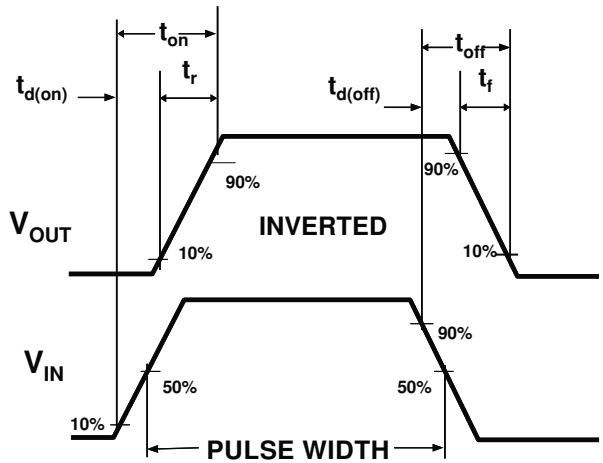
**Figure 1. Switching Test Circuit**



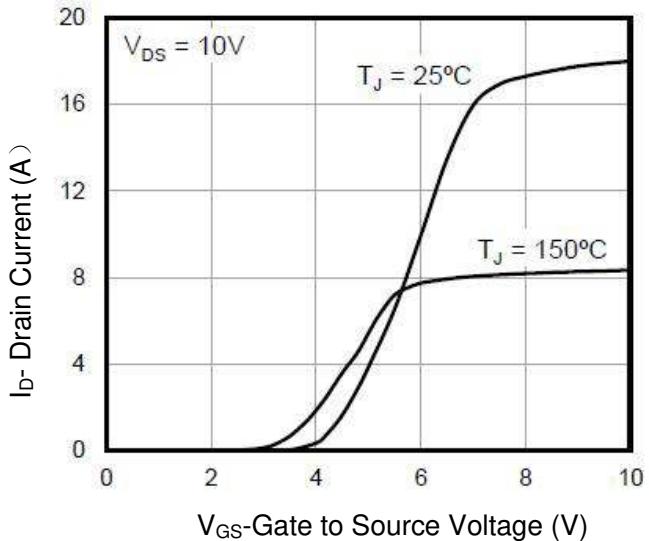
**Figure 3. Output Characteristics**



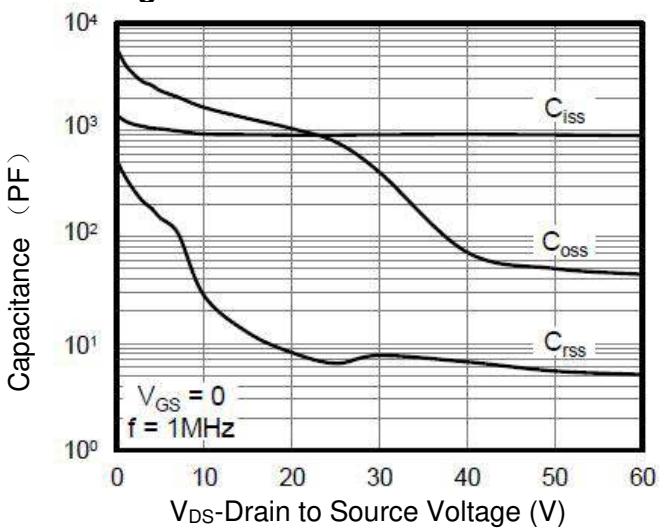
**Figure 5. On Resistance vs. Drain Current**



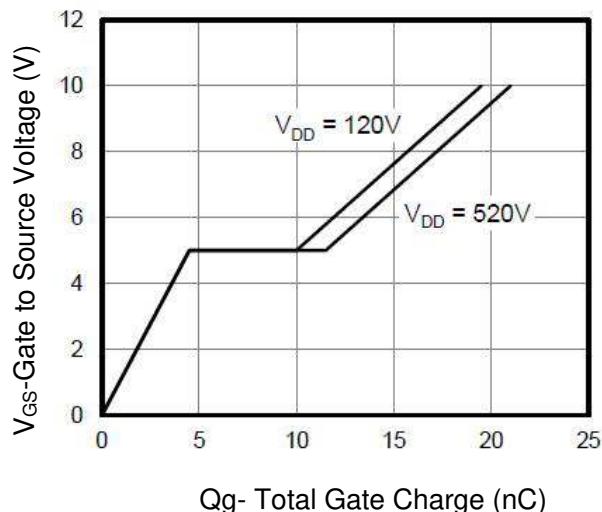
**Figure 2. Switching Waveforms**



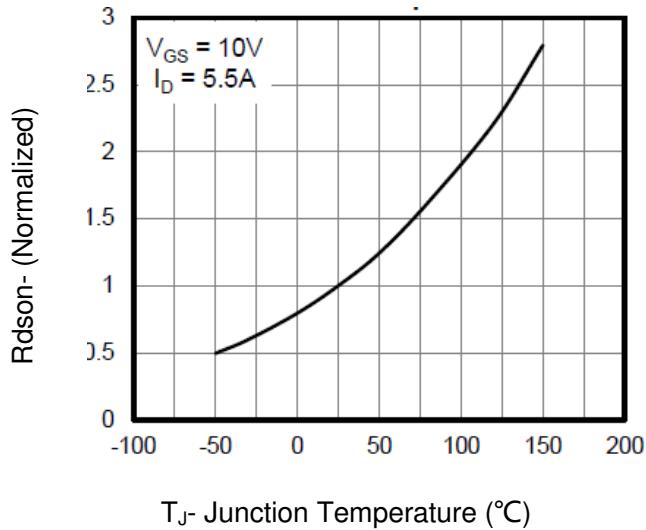
**Figure 4. Transfer Characteristics**



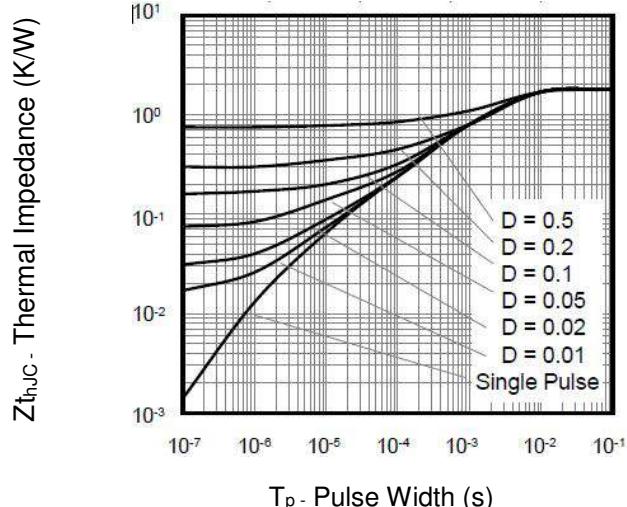
**Figure 6. Capacitance**



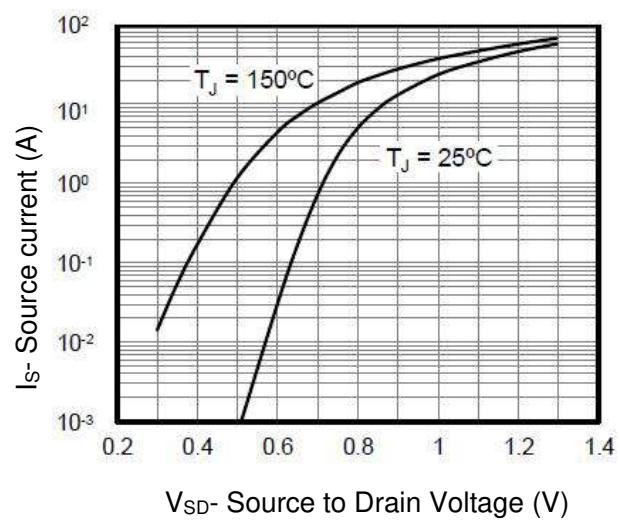
**Figure 7. Gate Charge**



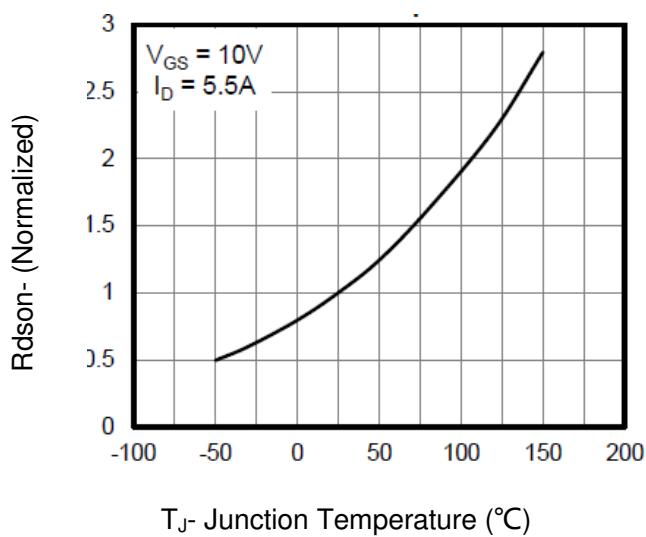
**Figure 9.  $R_{DS(on)}$  vs  $T_J$**



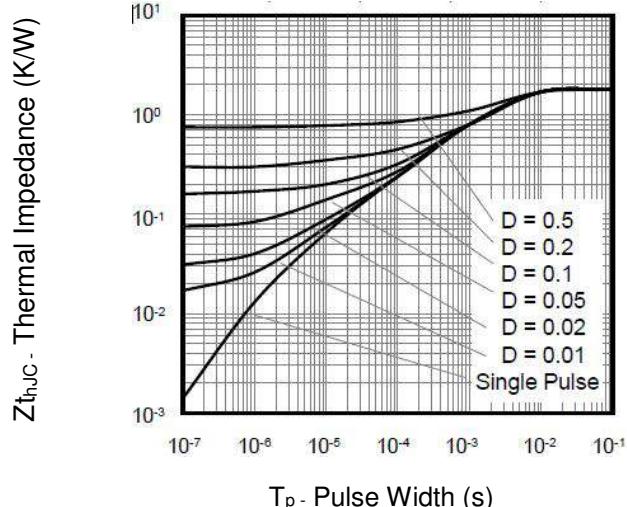
**Figure 11. Transient Thermal Impedance (TO-252, TO-220)**



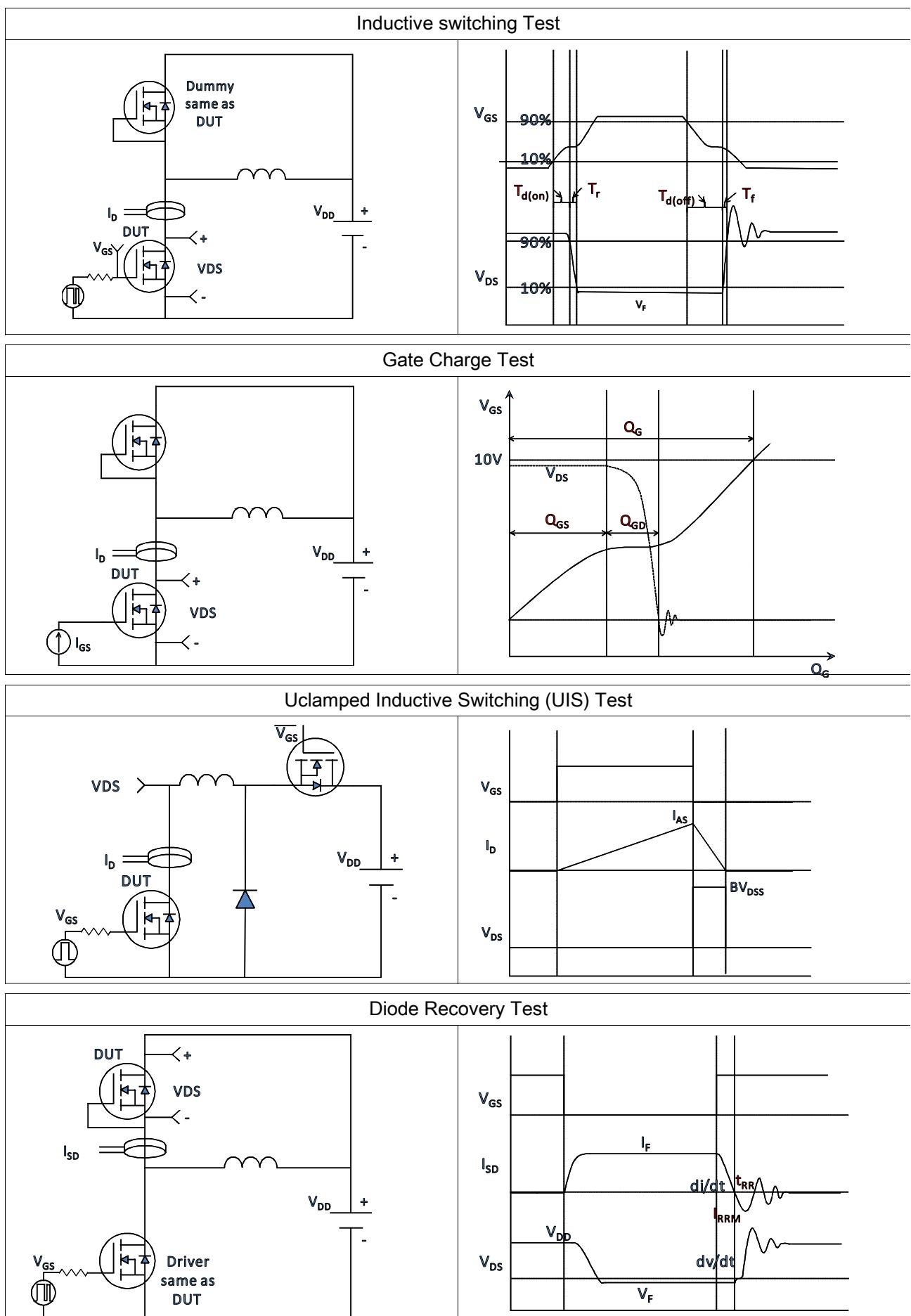
**Figure 8. Body Diode Forward Voltage**



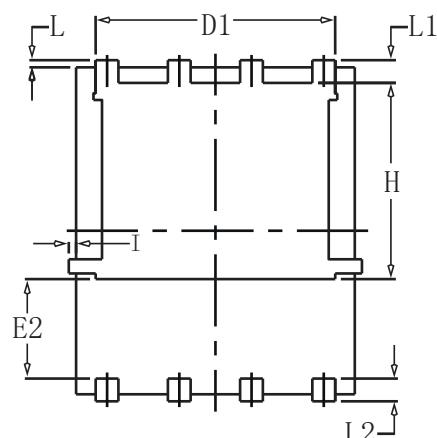
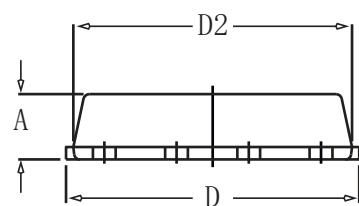
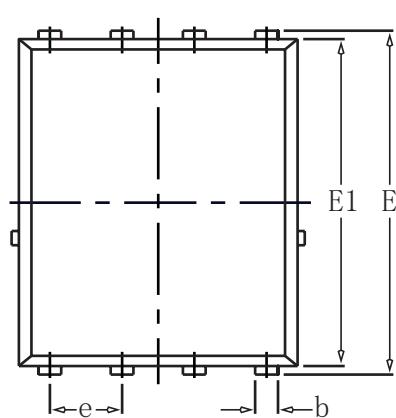
**Figure 10.  $V_{th}$  vs  $T_J$**



**Figure 12. Transient Thermal Impedance (TO-220F)**



## DFN5X6-8L Package information



SYMBOL	COMMON			
	MM		INCH	
	MIN	MAX	MIN	MAX
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.59	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	-	0.0630	-
e	1.27	BSC	0.05	BSC
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	-	0.18	-	0.0070